

**SB40100LCT**

## DUAL LOW VF SCHOTTKY RECTIFIER

**VOLTAGE**    **100 Volts**    **CURRENT**    **40 Amperes**

## FEATURES

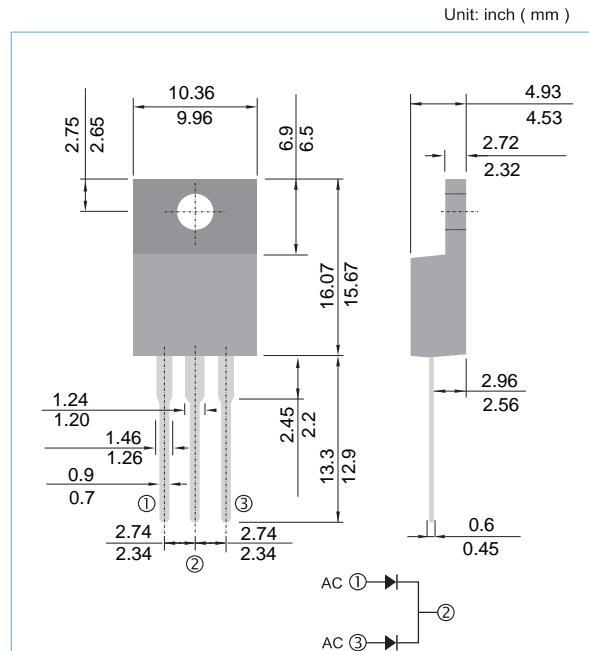
- Low forward voltage drop, low power losses
  - High efficiency operation
  - In compliance with EU RoHS 2002/95/EC directives

## MECHANICAL DATA

Case : TO-220AB, Plastic

Terminals : Solderable per MIL-STD-750, Method 2026

Weight: 0.055 ounces, 1.5615 grams.



**MAXIMUM RATINGS( $T_A=25^\circ\text{C}$  unless otherwise noted)**

PARAMETER	SYMBOL	VALUE	UNIT
Maximum repetitive peak reverse voltage	V <sub>RRM</sub>	100	V
Maximum average forward rectified current (Fig.3)	per device per diode	I <sub>F(AV)</sub> 40 20	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load per diode	per diode	I <sub>FSM</sub> 200	A
Typical thermal resistance	R <sub>θJC</sub>	2.0	°C/W
Operating junction	T <sub>J</sub>	- 40 to + 150	°C
Storage temperature range	T <sub>STG</sub>	- 40 to + 150	°C

## ELECTRICAL CHARACTERISTICS( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Breakdown voltage per diode	V <sub>BR</sub>	I <sub>R</sub> =1.0mA	103	120	-	V
Instantaneous forward voltage per diode <sup>(1)</sup>	V <sub>F</sub>	I <sub>F</sub> =20A	T <sub>J</sub> =25°C	-	0.80	V
		I <sub>F</sub> =20A	T <sub>J</sub> =125°C	-	0.71	0.74
Reverse current per diode <sup>(2)</sup>	I <sub>R</sub>	V <sub>R</sub> =70V	-	12	40	µA
		V <sub>R</sub> =100V	T <sub>J</sub> =25°C	-	500	µA
			T <sub>J</sub> =125°C	-	35	mA

Note.1 Pulse test : 380μs pulse width, 1% duty cycle

## 2. Pulse test : Pulse width < 2.5ms



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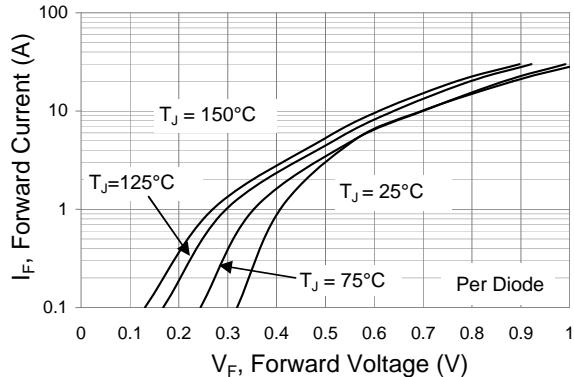


Fig.1 Typical Forward Characteristics

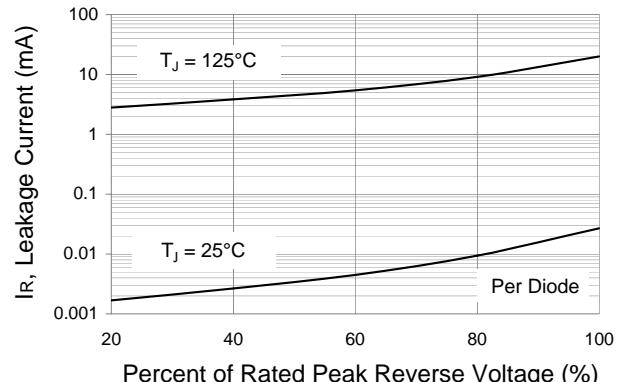


Fig.2 Typical Reverse Characteristics

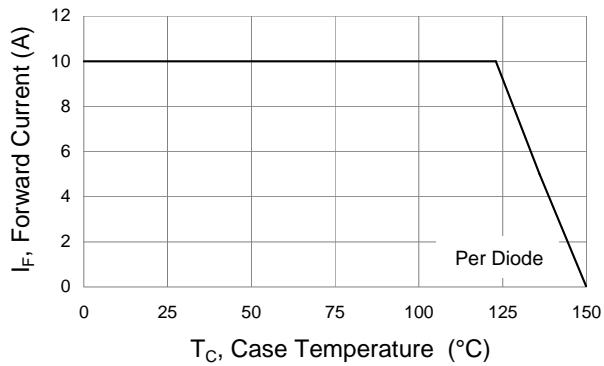


Fig.3 Forward Current Derating Curve

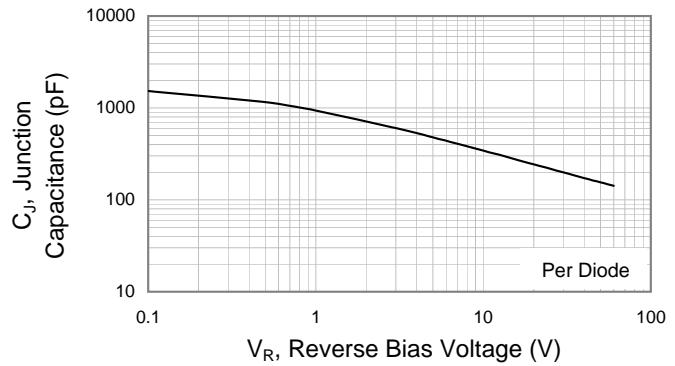


Fig.4 Typical Junction Capacitance